



DMN2024UFDF

20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	$22m\Omega @ V_{GS} = 4.5V$	7.1A
2017	26mΩ @ V _{GS} = 2.5V	6.5A
20V	36mΩ @ V _{GS} = 1.8V	5.5A
	50mΩ @ V _{GS} = 1.5V	4.7A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

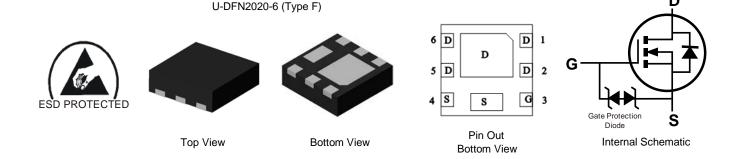
- Battery Management Application
- Power Management Functions
- DC-DC Converters

Features

- 0.6mm Profile—Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)



Ordering Information (Note 4)

Notes:

Part Number	Reel Size (inches)	Quantity Per Reel
DMN2024UFDF-7	7	3000
DMN2024UFDF-13	13	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Lead-free.



Marking Information

Site1

OA = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Kev

Year	2018		2019	2020		2021	2022		2023	2024		2025
Code	F		G	Н			J		K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1 .		-		_	-		-	-	<u> </u>		-

Site 2



OA = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: F = 2018)

W = Week (ex: a = week 27; z represents week 52 and 53)X = Internal code (ex: U = Monday)

Date Code Key								
Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	8	9	0	1	2	3	4	5
Week	1-26			27-52 53				
Code	A-Z			A-Z a-z z				
			·			•		
Internal Code	Sun	Mon	Τι	Je	Wed	Thu	Fri	Sat
Code	Т	U	١	/	W	Х	Y	Z



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±10	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			I _D	7.1 5.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	40	A
Continuous Source-Drain Diode Current		I _S	2.6	A	
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	12	A		
Avalanche Energy (Note 7) L = 0.1mH			Eas	8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.96	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{OJA}	130	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	1.67	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{OJA}	75	°C/W	
Thermal Resistance, Junction to Case (Note 6)	R _{eJC}	16	C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						÷
Drain-Source Breakdown Voltage	BV _{DSS}	20		—	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I _{DSS}	—	_	1	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	—	-	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)				-	-	
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
			15	22		$V_{GS} = 4.5V, I_D = 4A$
Static Drain-Source On-Resistance	Proven	_	17	26	mΩ	$V_{GS} = 2.5V, I_D = 4A$
	R _{DS(ON)}		20	36	11152	$V_{GS} = 1.8V, I_D = 4A$
			23	50		$V_{GS} = 1.5V, I_D = 4A$
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 5A$
DYNAMIC CHARACTERISTICS (Note 9)				-	-	
Input Capacitance	Ciss	—	647	—		
Output Capacitance	C _{oss}	-	78	—	pF	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V},$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	—	38	_		
Gate Resistance	Rg	—	628	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	—	7.1	—		
Total Gate Charge (V _{GS} = 10V)	Qg	-	0.9	—	nC	
Gate-Source Charge	Q _{gs}	—	0.7	—	nc	$V_{DS} = 10V, I_D = 6.5A$
Gate-Drain Charge	Q _{gd}	-	98	—		
Turn-On Delay Time	t _{D(ON)}	—	140	_		
Turn-On Rise Time	t _R	—	1024	_		$V_{DS} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	—	434	—	ns R _G =	$R_G = 6\Omega, R_L = 10\Omega, I_D = 1A$
Turn-Off Fall Time	t _F	—	245	—		
Reverse Recovery Time	t _{RR}	_	149	—	ns	I _F = 1A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	647	—	nC	I _F = 1A, di/dt = 100A/µs

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

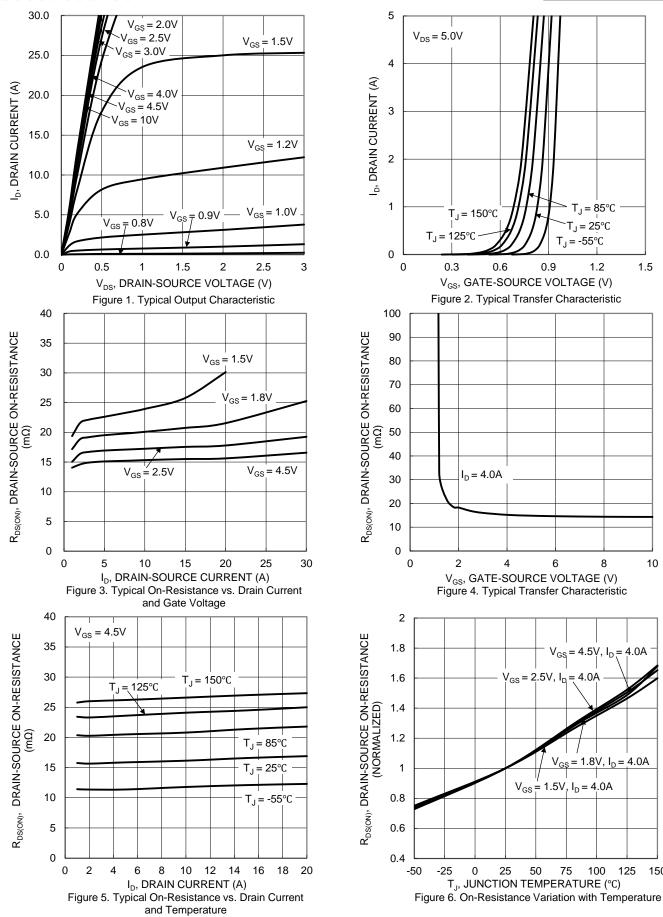
8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.



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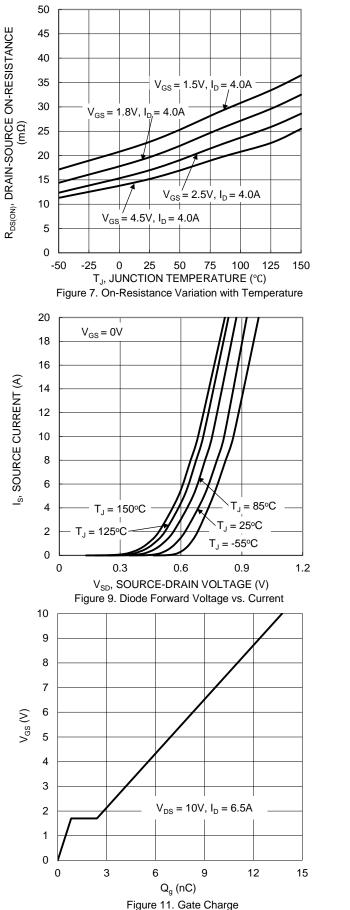
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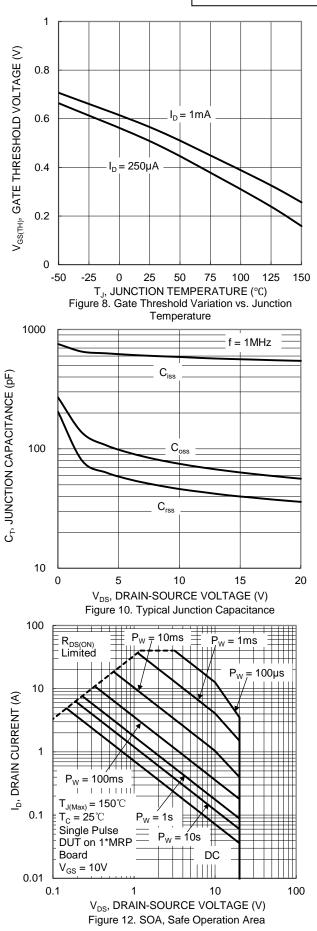


DMN2024UFDF Datasheet number: DS40595 Rev. 7 - 2 150



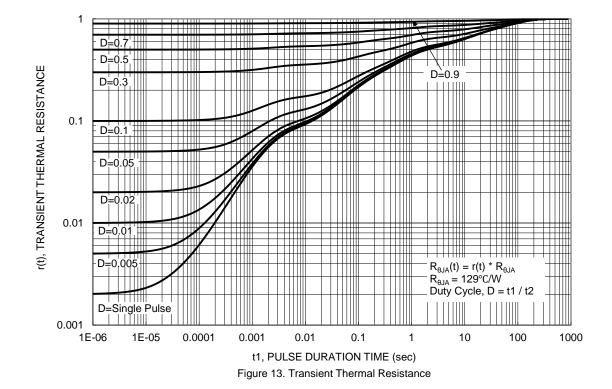
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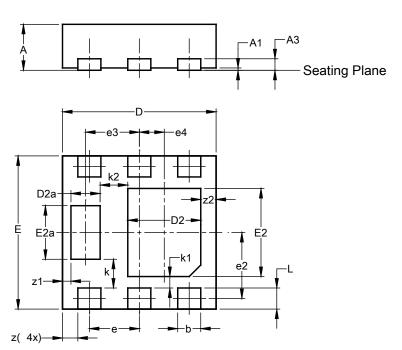






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

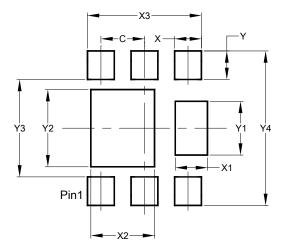


	U-DFN2020-6 (Type F)								
Dim	Min	Max	Тур						
Α	0.57 0.63 0.60								
A1	0.00	0.05	0.03						
A3	-	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
ш	1.95	2.05	2.00						
E2	1.05	1.25	1.15						
E2a	0.65	0.75	0.70						
e	0.65 BSC								
e2	0.863 BSC								
e3		0.70 BS	С						
e4	C).325 BS	SC						
k		0.37 BS							
k1	0.15 BSC								
k2	0.36 BSC								
L	0.225 0.325 0.275								
z		0.20 BS							
z1).110 BS							
z2		0.20 BS	-						
All D	imens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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